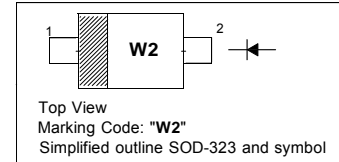


Silicon Epitaxial Planar Switching Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Reverse Voltage	V_R	75	V
Continuous Forward Current	I_F	250	mA
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	at $t = 1\text{ s}$ 0.5	A
		at $t = 1\text{ ms}$ 1	
		at $t = 1\text{ }\mu\text{s}$ 4	
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit			
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 50\text{ mA}$ at $I_F = 150\text{ mA}$	V_F	0.715 0.855 1 1.25	V			
Reverse Current at $V_R = 25\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 25\text{ V}, T_J = 150\text{ }^\circ\text{C}$ at $V_R = 75\text{ V}, T_J = 150\text{ }^\circ\text{C}$		I_R		30 1 30 50	nA μA μA μA	
Diode Capacitance at $V_R = 0\text{ V}, f = 1\text{ MHz}$				C_{tot}	1.5	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}, I_R = 1\text{ mA}, R_L = 100\text{ }\Omega$				t_{rr}	4	ns



Typical Characteristics

Fig 1. Power Dissipation vs. Temperature

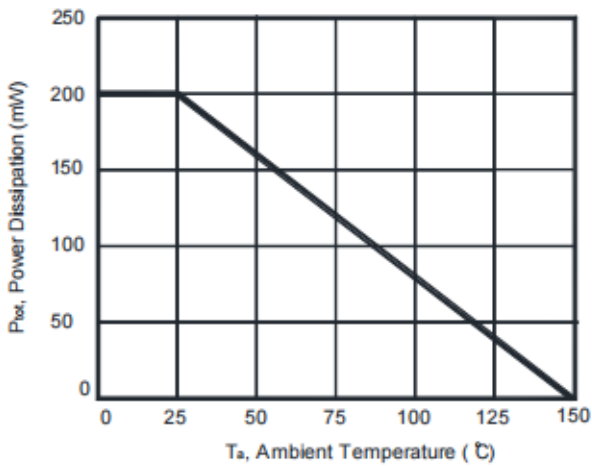


Fig 2. Total Capacitance vs. Reverse Voltage

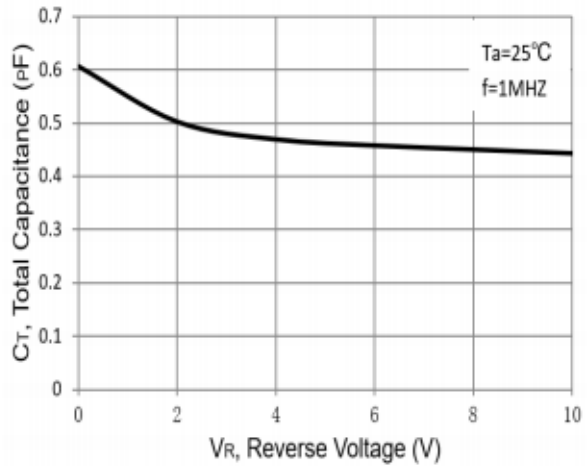


Fig 3. Reverse Current vs. Reverse Voltage

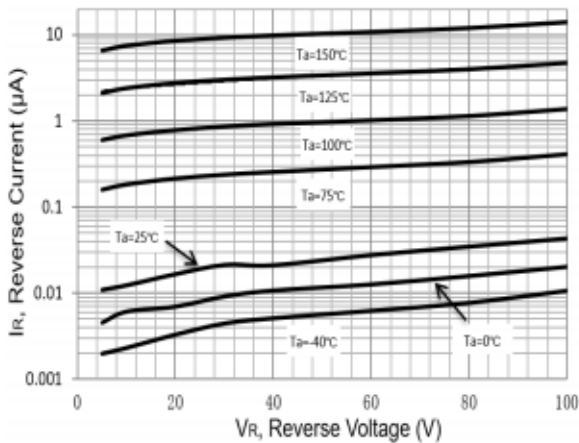
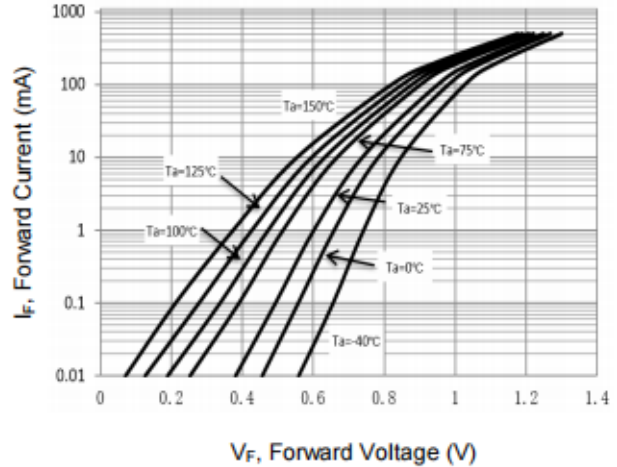


Fig 4. Forward Characteristics





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SOD-323

BAS216WS

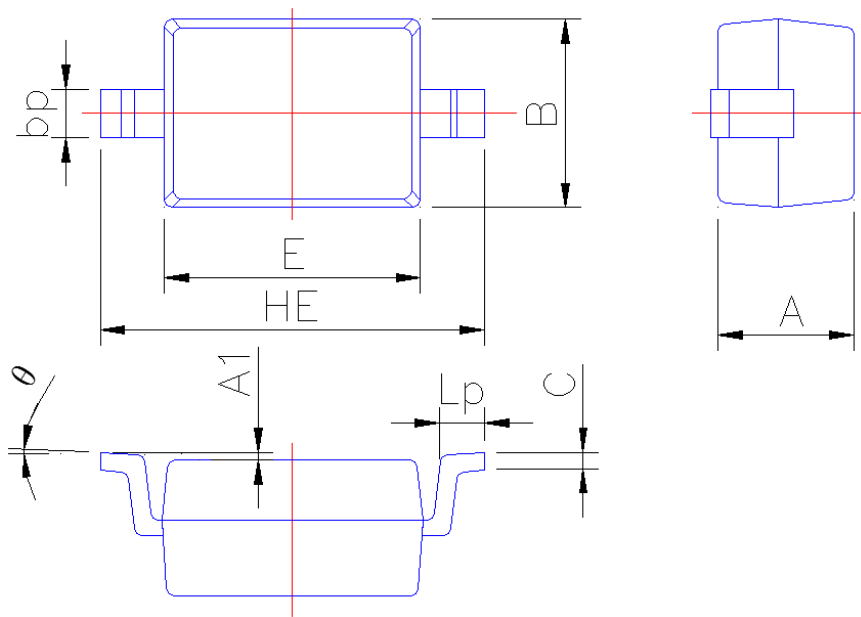


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.15
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.40
C	0.09	0.150
E	1.60	1.80
HE	2.30	2.70
Lp	0.20	0.40
θ	0°	5°